



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Surface Mount Package Suited for Automated Assembly

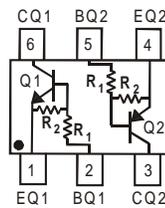
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.006 grams (Approximate)

R ₁ (Nom)	R ₂ (Nom)
22kΩ	22kΩ



Top View



Device Schematic

Absolute Maximum Ratings - NPN Section (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Supply Voltage <Pin: (6) to (1)>	V _{CC}	50	V
Input Voltage <Pin: (2) to (1)>	V _{IN}	-10 to +40	V
Output Current	I _O	30	mA
Output Current	I _C (Max)	100	mA

Absolute Maximum Ratings - PNP Section (@T_A = +25°C, unless otherwise specified.)

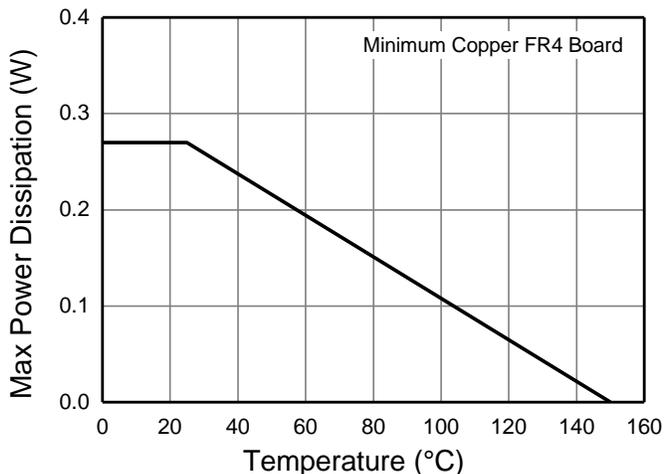
Characteristic	Symbol	Value	Unit
Supply Voltage <Pin: (4) to (3)>	V _{CC}	50	V
Input Voltage <Pin: (5) to (4)>	V _{IN}	+10 to -40	V
Output Current	I _O	-30	mA
Output Current	I _C (Max)	-100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

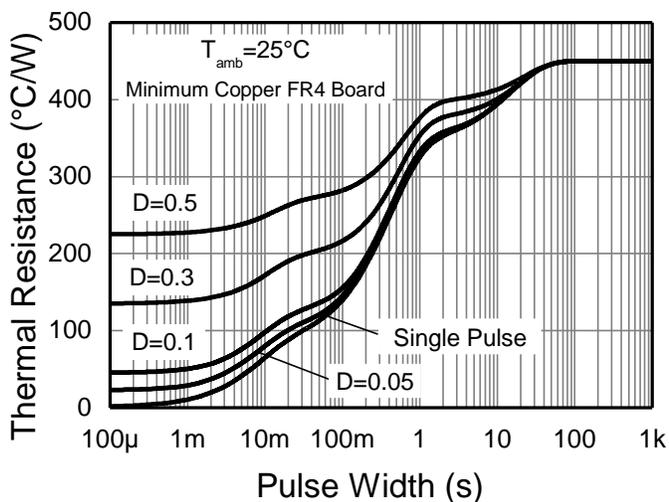
Characteristic	Symbol	Value	Unit
Power Dissipation (Notes 6 & 7)	P _D	270	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	R _{θJA}	450	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 6. Mounted on FR4 PC Board with minimum recommended pad layout
 7. 150mW per element must not be exceeded.

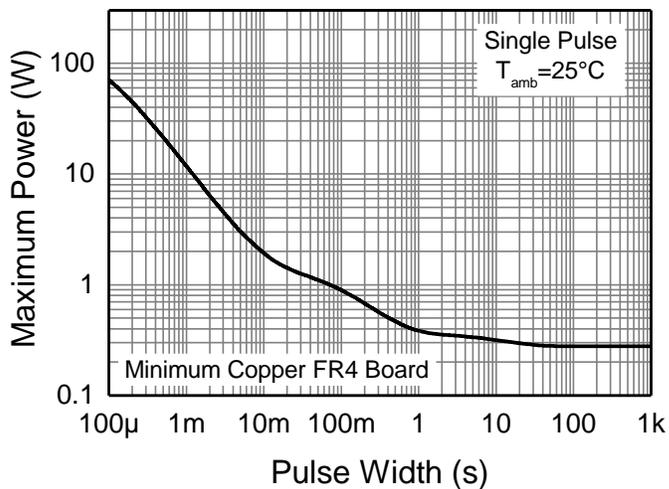
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

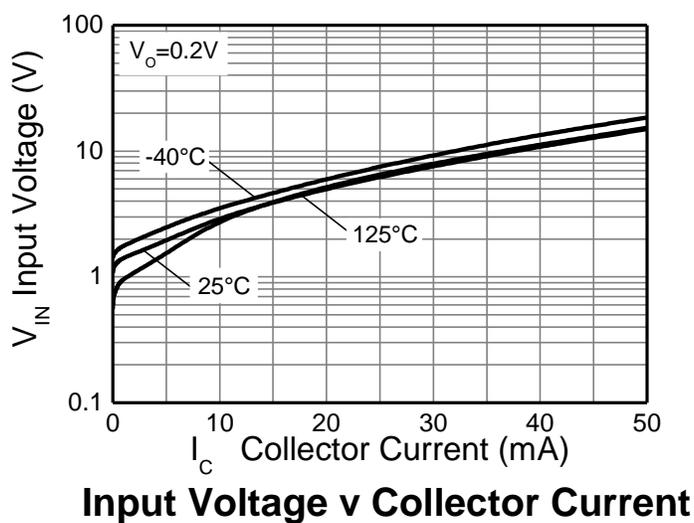
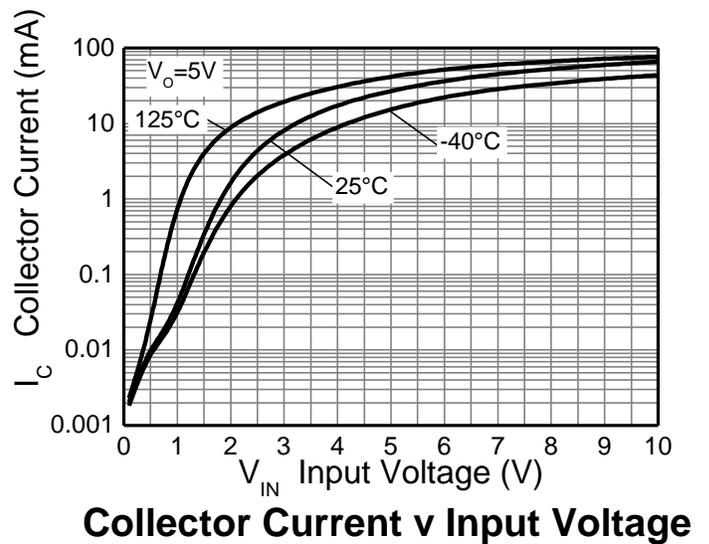
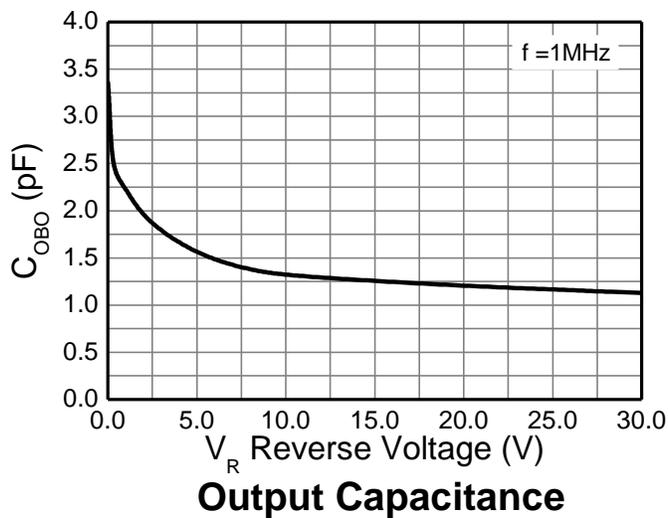
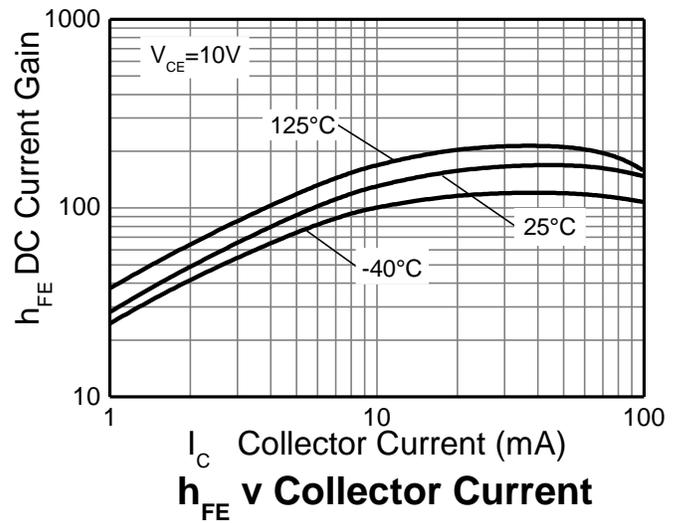
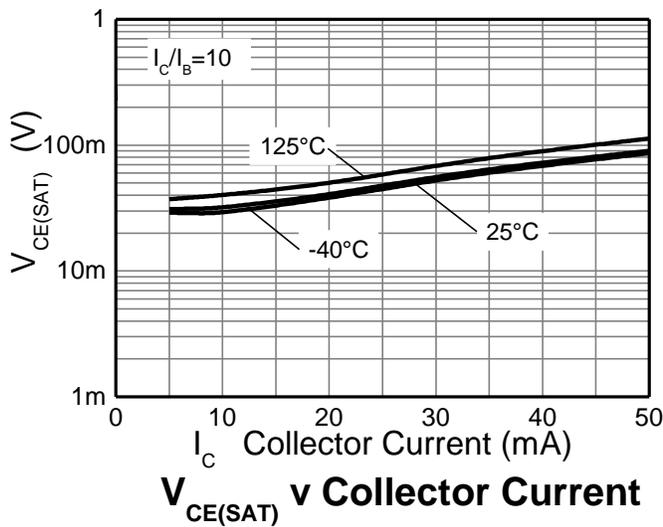
Electrical Characteristics - NPN Section (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	$V_{I(OFF)}$	0.5	1.1	—	V	$V_{CC} = 5V, I_O = 100\mu\text{A}$
	$V_{I(ON)}$	—	1.9	3.0		$V_O = 0.3V, I_O = 5\text{mA}$
Output Voltage	$V_{O(ON)}$	—	0.1	0.3	V	$I_O/I_I = 10\text{mA} / 0.5\text{mA}$
Input Current	I_I	—	—	0.36	mA	$V_I = 5V$
Output Current	$I_{O(OFF)}$	—	—	0.5	μA	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	G_I	60	—	—	—	$V_O = 5V, I_O = 5\text{mA}$
Input Resistor (R_1) Tolerance	ΔR_1	-30	—	+30	%	—
Resistance Ratio Tolerance	$\Delta R_2/R_1$	-20	—	+20	%	—
Gain-Bandwidth Product	f_T	—	250	—	MHz	$V_{CE} = 10V, I_E = 5\text{mA}, f = 100\text{MHz}$

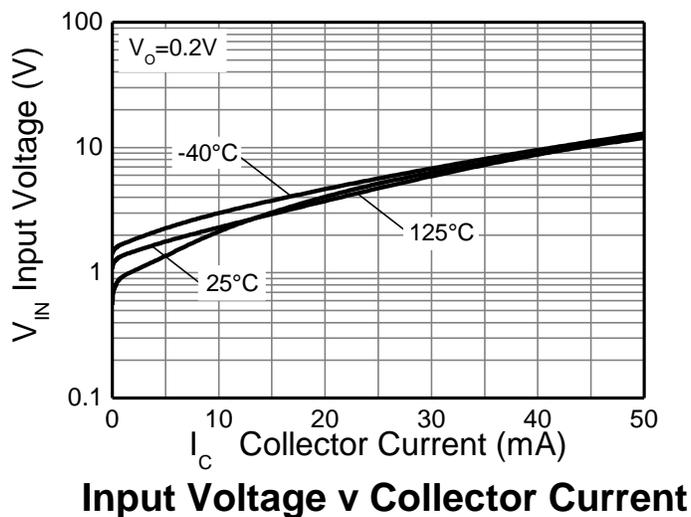
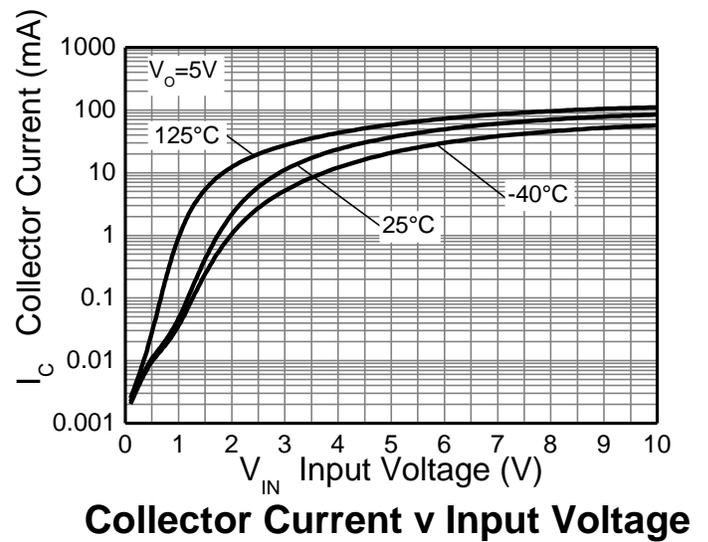
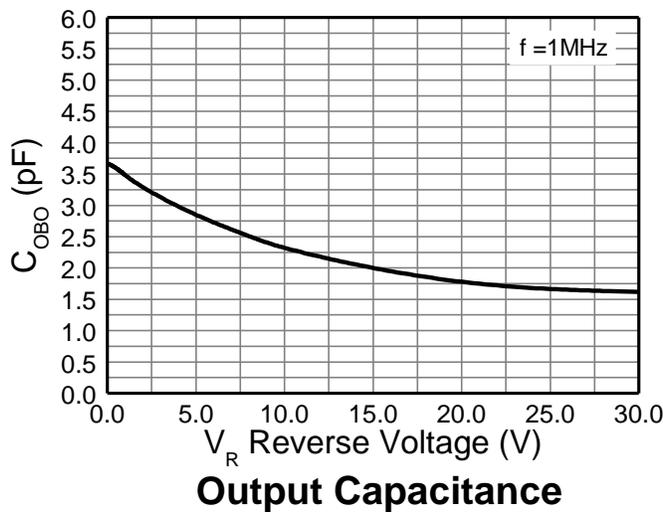
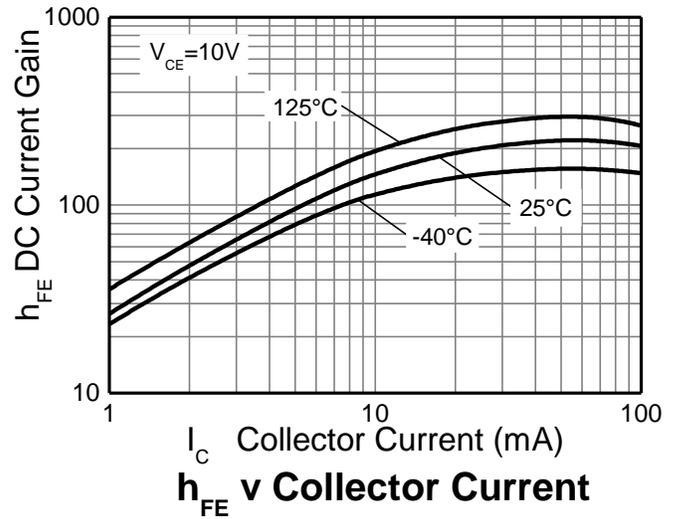
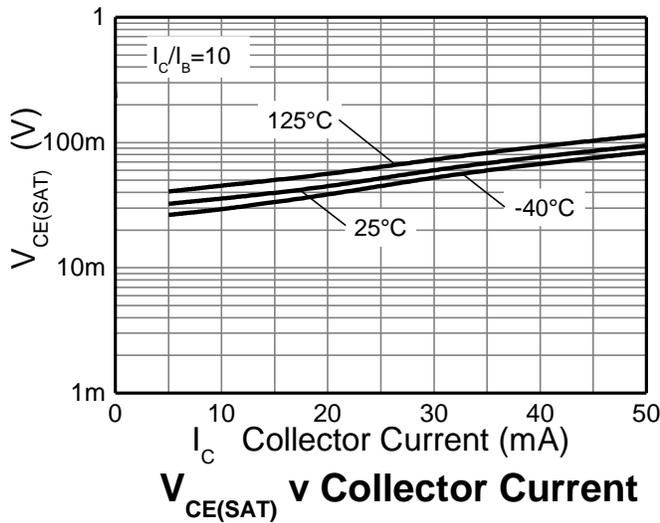
Electrical Characteristics - PNP Section (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	$V_{I(OFF)}$	-0.5	-1.1	—	V	$V_{CC} = -5V, I_O = -100\mu\text{A}$
	$V_{I(ON)}$	—	-1.9	-3.0		$V_O = -0.3V, I_O = -5\text{mA}$
Output Voltage	$V_{O(ON)}$	—	-0.1	-0.3	V	$I_O/I_I = -10\text{mA} / -0.5\text{mA}$
Input Current	I_I	—	—	-0.36	mA	$V_I = -5V$
Output Current	$I_{O(OFF)}$	—	—	-0.5	μA	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	G_I	60	—	—	—	$V_O = -5V, I_O = -5\text{mA}$
Input Resistor (R_1) Tolerance	ΔR_1	-30	—	+30	%	—
Resistance Ratio Tolerance	$\Delta R_2/R_1$	-20	—	+20	%	—
Gain-Bandwidth Product	f_T	—	250	—	MHz	$V_{CE} = -10V, I_E = -5\text{mA}, f = 100\text{MHz}$

Typical Electrical Characteristics – NPN Section (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

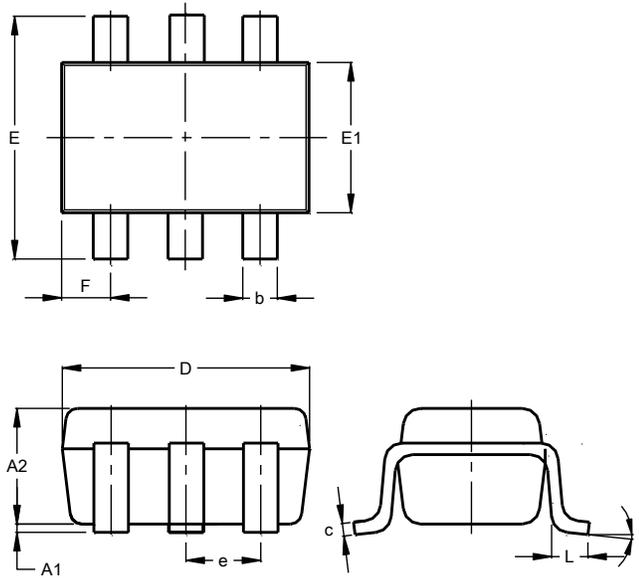


Typical Electrical Characteristics – PNP Section (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

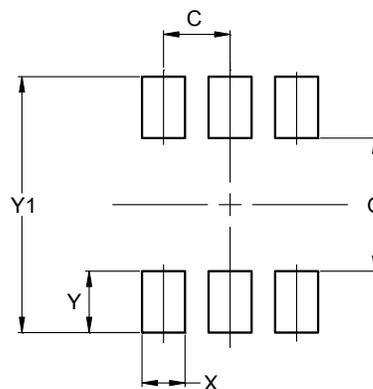
SOT363



SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500